

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The ASI VHB40-28F is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	5.0 A
$V_{CBO}$	65 V
$V_{CE0}$	35 V
$V_{EBO}$	4.0 V
$P_{DISS}$	60 W
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	2.9 °C/W

**PACKAGE STYLE .380 4L FLG**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

**ORDER CODE: ASI10726**

**CHARACTERISTICS**  $T_C = 25\text{ }^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 200\text{ mA}$		35			V
$BV_{CES}$	$I_C = 200\text{ mA}$		65			V
$BV_{CBO}$	$I_C = 10\text{ mA}$		65			V
$BV_{EBO}$	$I_E = 10\text{ mA}$		4.0			V
$I_{CBO}$	$V_{CB} = 30\text{ V}$				1.0	mA
$I_{CES}$	$V_{CE} = 30\text{ V}$				10	mA
$h_{FE}$	$V_{CE} = 5.0\text{ V}$	$I_C = 500\text{ mA}$	5.0		200	---
$C_{ob}$	$V_{CB} = 30\text{ V}$	$f = 1.0\text{ MHz}$			65	pF
$P_G$	$V_{CE} = 28\text{ V}$	$P_{IN} = 7.0\text{ W}$	7.6			dB
$\eta_C$			60			%